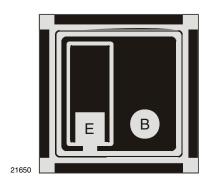
COMPLIANT



Vishay Semiconductors

Silicon NPN Phototransistor

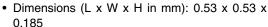


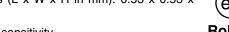
DESCRIPTION

T1090P is a silicon NPN phototransistor chip with high radiant sensitivity, sensitive to visible and near infrared radiation.

FEATURES

- Package type: chip
- Package form: single chip







- · High radiant sensitivity
- · Suitable for visible and near infrared radiation
- Fast response times
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



· Detector in electronic control and drive circuits

high APPLICATIONS

GENERAL INFORMATION

The datasheet is based on Vishay optoelectronics sample testing under certain predetermined and assumed conditions, and is provided for illustration purpose only. Customers are encouraged to perform testing in actual proposed packaged and used conditions. Vishay optoelectronics die products are tested using Vishay optoelectronics based quality assurance procedures and are manufactured using Vishay optoelectronics established processes. Estimates such as those described and set forth in this datasheet for semiconductor die will vary depending on a number of packaging, handling, use, and other factors. Therefore sold die may not perform on an equivalent basis to standard package products.

PRODUCT SUMMARY				
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.1} (nm)	
T1090P	0.43 to 0.77	± 60	440 to 1070	

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
T1090P-SD-F	Wafer sawn on foil with disco frame	MOQ: 50 000 pcs	Chip		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Collector emitter voltage		V _{CEO}	70	V	
Emitter collector voltage		V _{ECO}	5	V	
Collector current		I _C	50	mA	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg1}	- 40 to + 100	°C	
Storage temperature range on foil		T _{stg2}	- 40 to + 50	°C	

Note

 T_{amb} = 25 °C, unless otherwise specified

Silicon NPN Phototransistor



BASIC CHARACTERISTICS (1)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V
Collector emitter dark current	V _{CE} = 20 V, E = 0	I _{CEO}		1		nA
Collector light current (Vishay selection type ³)	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_{CE} = 5 \text{ V}$	I _{ca}	0.43		0.77	mA
Wavelength of peak sensitivity		λ_{p}		825		nm
Range of spectral bandwidth		λ _{0.1}		440 to 1070		nm
Rise time	$V_{CE} = 5 \text{ V}, I_{C} = 2 \text{ mA}, R_{L} = 100 \Omega$	t _r , t _f		4.3		μs
Fall time	$V_{CE} = 5 \text{ V}, I_{C} = 2 \text{ mA}, R_{L} = 100 \Omega$	t _r , t _f		7.7		μs

Note

- $^{(1)}$ T_{amb} = 25 $^{\circ}$ C, unless otherwise specified
- (2) The measurements are based on samples of die which are mounted on a TO-header without resin coating
- (3) Specific selection types possible

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

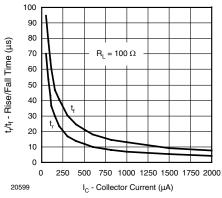


Fig. 1 - Rise/Fall Time vs. Collector Current

MECHANICAL DIMENSIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Length of chip edge (x-direction)	L _x		0.52		mm
Length of chip edge (y-direction)	L _y		0.52		mm
Die height	Н		0.185		mm
Diameter of bond pad base	d		0.1		mm
Bond pad emitter	axb		0.1 x 0.1		mm ²

ADDITIONAL INFORMATION (1)				
Frontside metallization, base (B), emitter (E)	Aluminum			
Backside metallization, collector	AuSb			
Dicing	Sawing			
Die bonding technology	Epoxy bonding			

Note

(1) All chips are checked in accordance with the Vishay Semiconductor, specification of visual inspection FVOV6870.

The visual inspection shall be made in accordance with the "specification of visual inspection as referenced". The visual inspection of chip backside is performed with stereo microscope with incident light and 40x to 80x magnification.

The quality inspection (final visual inspection) is performed by production. An additional visual inspection step as special release procedure by QM is not installed.





Silicon NPN Phototransistor

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HANDLING AND STORAGE CONDITIONS

- The hermetically sealed shipment lots shall be opened in temperature and moisture controlled cleanroom environment only. It is mandatory to follow the rules for disposition of material that can be hazardous for humans and environment.
- Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
- Singulated die are not to be handled with tweezers. A vacuum wand with non metallic ESD protected tip should be used.

PACKING

Chips are fixed on adhesive foil. Upon request the foils can be mounted on plastic frame or disco frame. For shipment, the wafers are arranged to stacks and hermetically sealed in plastic bags to ensure protection against environmental influence (humidity and contamination).

Use for recycling reliable operators only. We can help getting in touch with your nearest sales office. By agreement we will take back packing material, if it is sorted. You will have to bear the costs of transport. We will invoice you for any costs incurred for packing material that is returned unsorted or which we are not obliged to accept.



Vishay

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